



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>



NTE643 Silicon Dual Schottky Rectifier 200V, 10 Amp, TO220 Type Package

Features:

- Schottky Barrier Chip
- Guard Ring for Transient Protection
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Surge Current capability

Maximum Ratings and Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified. Single Phase, Half Wave, 60Hz, Resistive or Inductive load. For capacitive load, derate current by 20%)

Peak Repetitive Reverse Voltage, V_{RRM}	200V
Working Peak Reverse Voltage, V_{RWM}	200V
DC Blocking Voltage, V_R	200V
RMS Reverse Voltage, $V_{R(RMS)}$	140V
Average Rectified Output Current ($T_C = +95^\circ\text{C}$), I_O	10A
Non-Repetitive Peak Forward Surge Current, I_{FSM} (8.3ms Single Half Sine-Wave Superimposed on Rated Load)	150A
Forward Voltage ($I_F = 5A$), V_{FM}	0.92V
Peak Reverse Current (At Rated DC Blocking Voltage), I_{RM}	
$T_A = +25^\circ\text{C}$	0.5mA
$T_A = +100^\circ\text{C}$	50mA
Typical Junction Capacitance (Note 1), C_j	700pF
Operating Junction Temperature Range, T_J	-65° to $+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65° to $+150^\circ\text{C}$

Note 1. Measured at 1MHz and applied reverse voltage of 4VDC.

